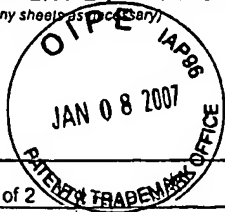


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STATEMENT BY APPLICANT**

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Sheet 1 of 2

Complete if Known

Application Number 10/789,042
Filing Date February 27, 2004
First Named Inventor Ahn, Kie
Group Art Unit 2815
Examiner Name Richards, N.

Attorney Docket No: 1303.050US2

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EXAMINER

DATE CONSIDERED

3/30/07

Substitute Disclosure Statement Form (PTO-1449)

* EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant. 1 Applicant's unique citation designation number (optional) 2 Applicant is to place a check mark here if English language Translation is attached

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<i>Complete If Known</i>	
Application Number	10/789,042
Filing Date	February 27, 2004
First Named Inventor	Ahn, Kie
Group Art Unit	2815
Examiner Name	Richards, N.

Sheet 2 of 2

Attorney Docket No: 1303.050US2

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NA		AHN, KIE Y., et al., "LANTHANIDE YTTRIUM ALUMINUM OXIDE DIELECTRIC FILMS", U.S. Application Serial No. 11/297,567, filed December 8, 2005	
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DATE CONSIDERED 3/30/07

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S/N 10/789,042

PATENT

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant: Kie Y. Ahn et al.

Examiner: N. D. Richards

Serial No.: 10/789,042

Group Art Unit: 2815

Filed: February 27, 2004

Docket: 1303.050US2

Title: LAALO3 FILMS (AS AMENDED)

COMMUNICATION CONCERNING RELATED APPLICATIONS

MS RCE

Commissioner for Patents

P.O. Box 1450

Alexandria, VA 22313-1450

Applicants would like to bring to the Examiner's attention the following related applications in the above-identified patent application:

<u>Serial/Patent No.</u>	<u>Filing Date/Issue Date</u>	<u>Attorney Docket</u>	<u>Title</u>
11496196	July 31, 2006	1303.068US4	MEMORY UTILIZING OXIDE-CONDUCTOR NANOLAMINATES
10443021 6970053	May 22, 2003	1303.137US1	ATOMIC LAYER DEPOSITION (ALD) HIGH PERMEABILITY LAYERED MAGNETIC FILMS TO REDUCE NOISE IN HIGH SPEED INTERCONNECTION
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Handwritten signature and date 3/30/07

COMMUNICATION CONCERNING RELATED APPLICATIONS

Serial Number: 10/789,042

Filing Date: February 27, 2004

Title: LAALO3 FILMS (AS AMENDED)

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Dkt: 1303.050US2

FILMS AS GATE DIELECTRICS

11457987 July 17, 2006 1303.061US5 ATOMIC LAYER DEPOSITED
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DIELECTRIC LAYER

~~Continuations and divisionals may be later filed on the cases listed above, or cited to the Examiner in any previous Communication Concerning Related Applications. Applicants request that the Examiner review all continuations and divisionals of the above-listed or previously-cited patent applications before allowing the claims of the present patent application.~~

Respectfully submitted,
KIE Y. AHN ET AL.

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Date 5 January 2007

By

David R. Cochran
Reg. No. 46,632

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4/2/07 3/30/07